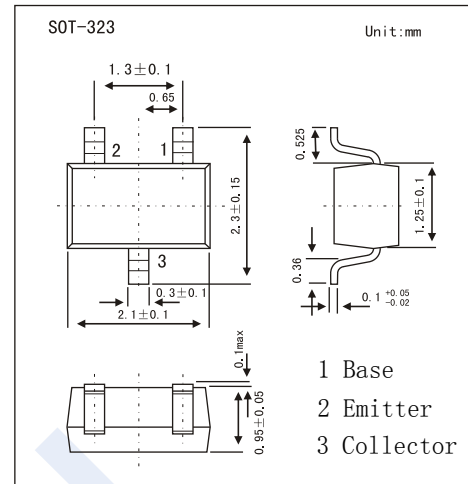


PNP Transistors

2SA1979UF

■ Features

- Large collector current :
 $I_{CMax} = -500\text{mA}$
- Complements to 2SC5342UF

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-40	V
Collector - Emitter Voltage	V_{CEO}	-32	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100\ \mu\text{A}$, $I_E = 0$	-40			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1\ \text{mA}$, $I_B = 0$	-32			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100\ \mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -40\text{V}$, $I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}$, $I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$			-0.25	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -1\text{V}$, $I_C = -100\text{mA}$	70		240	
Collector output capacitance	C_{ob}	$V_{CB} = -6\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		7.5		pF
Transition frequency	f_T	$V_{CE} = -6\text{V}$, $I_C = -20\text{mA}$		200		MHz

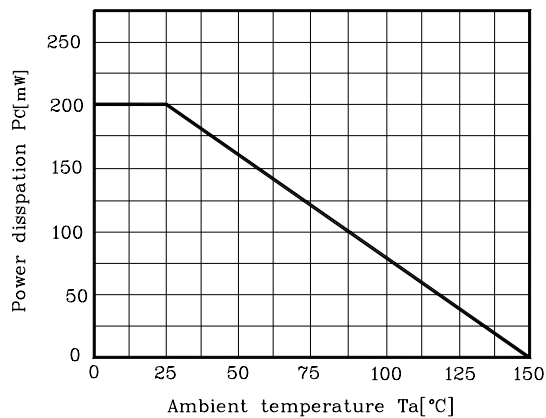
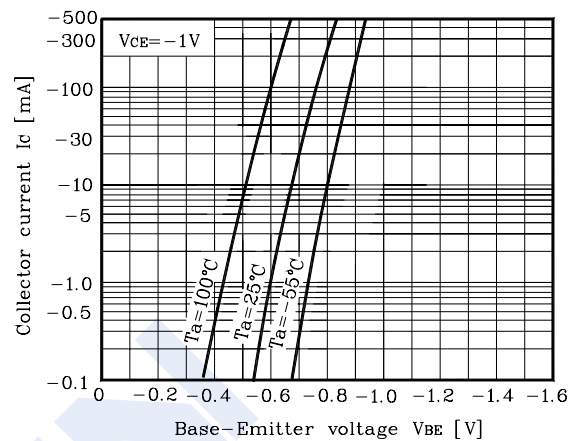
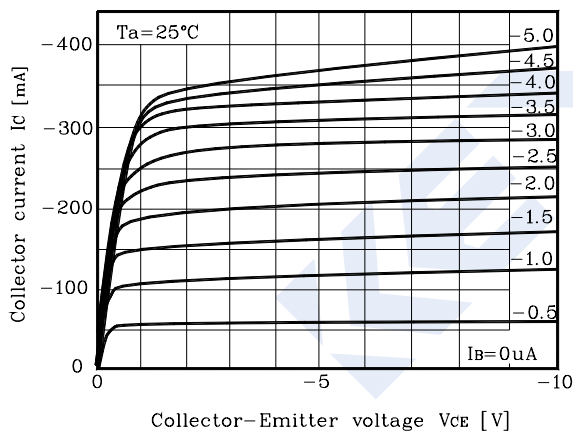
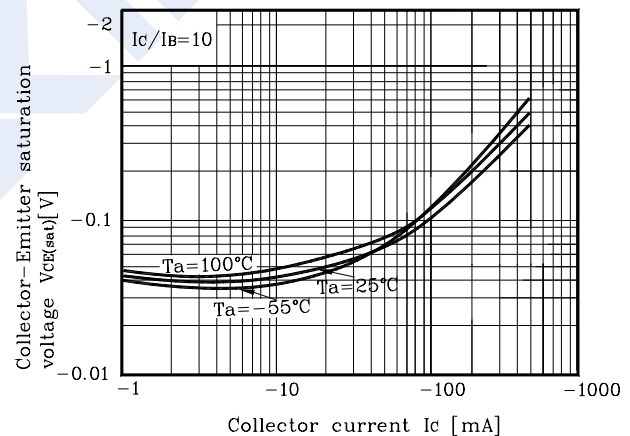
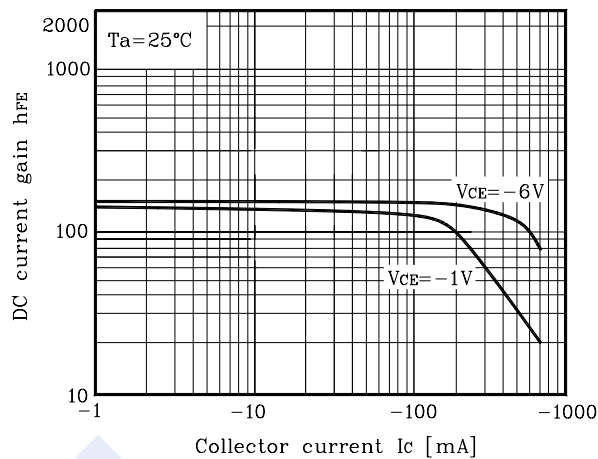
■ Classification of h_{FE}

Type	2SA1979UF-O	2SA1979UF-Y
Range	70-140	120-240
Marking	AO	AY

PNP Transistors

2SA1979UF

■ Typical Characteristics

Fig. 1 $P_C - T_a$ Fig. 2 $I_C - V_{BE}$ Fig. 3 $I_C - V_{CE}$ Fig. 4 $V_{CE(sat)} - I_C$ Fig. 5 $h_{FE} - I_C$ Fig. 6 $h_{FE} - I_C$ 